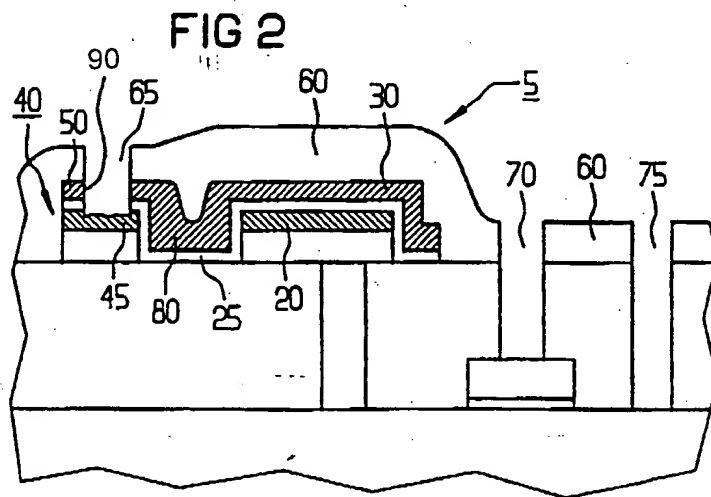
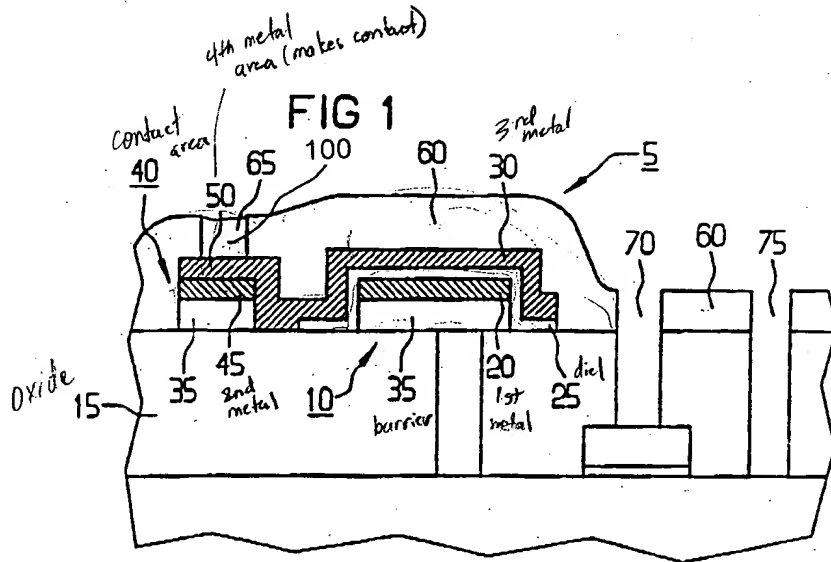


296
warren

1/1



This cross-sectional view shows a semiconductor device with a substrate 15. A gate stack 10 is formed on the substrate, consisting of a gate dielectric 30 and a gate electrode 35. A trench 20 is formed in the substrate, with a trench dielectric 25 lining its side walls. A gate electrode 35 is positioned within the trench. A gate electrode 40 is formed on the top surface of the gate stack. A gate electrode 45 is formed on the top surface of the gate stack. A gate electrode 50 is formed on the top surface of the gate stack. A gate electrode 60 is formed on the top surface of the gate stack. A gate electrode 65 is formed on the top surface of the gate stack. A gate electrode 70 is formed on the top surface of the gate stack. A gate electrode 75 is formed on the top surface of the gate stack. A gate electrode 80 is formed on the top surface of the gate stack. A gate electrode 85 is formed on the top surface of the gate stack. A gate electrode 90 is formed on the top surface of the gate stack. A gate electrode 95 is formed on the top surface of the gate stack. A gate electrode 100 is formed on the top surface of the gate stack.